

IN THE ABSTRACT:

Please replace the earlier submitted revised Abstract with the amended Abstract presented on the next page.

ABSTRACT

To a polycrystalline silicon layer crystallized by irradiation with laser light, a mixed gas comprised of ozone gas and H₂O or N₂O gas is fed at a processing temperature of 500°C or below, or the polycrystalline silicon layer is previously treated with a solution such as ozone water or an aqueous NH₃/hydrogen peroxide solution, followed by oxidation treatment with ozone, to form a silicon oxide layer with a thickness of 4 nm or more at the surface of the polycrystalline silicon layer for forming a thin-film transistor having characteristics that are less varying on a glass substrate previously not annealed.
